

1SS510WT

SILICON EPITAXIAL PLANAR DIODE

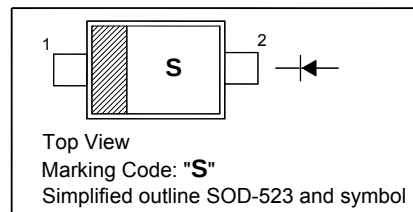
Band Switching Diode

Applications

- For VHF tuner band RF attenuator
- AGC for FM tuner

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Voltage at $I_R = 10\ \mu\text{A}$	V_R	50	-	-	V
Reverse Current at $V_R = 50\ \text{V}$	I_R	-	-	0.1	μA
Total Capacitance at $V_R = 50\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	0.25	-	pF
Series Resistance at $I_F = 5\ \text{mA}$, $f = 100\ \text{MHz}$	r_s	-	1.5	-	Ω

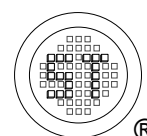


Fig. 1 I_C - T_a

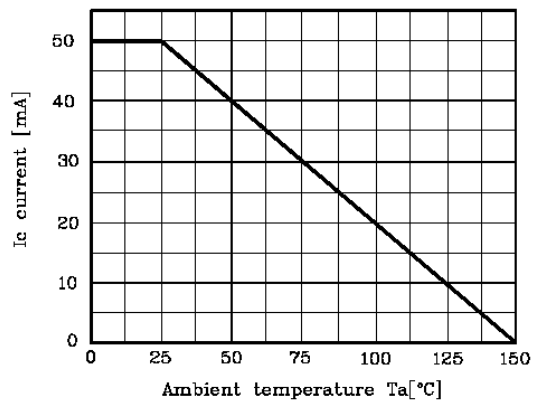


Fig. 2 I_F - V_F

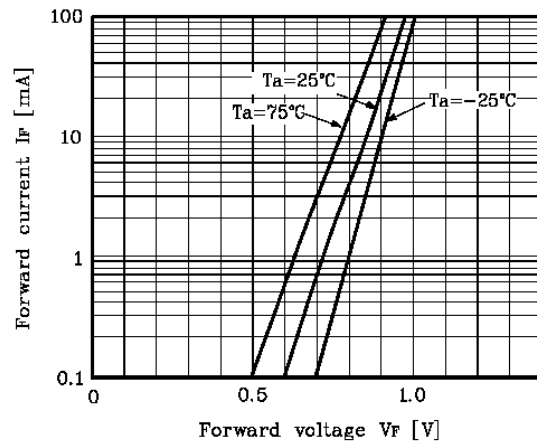


Fig. 3 C_T - V_R

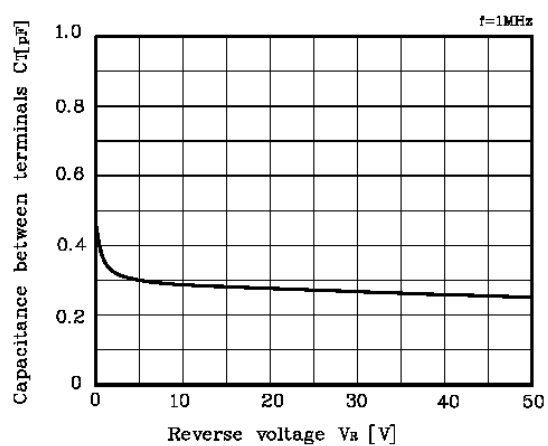
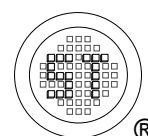
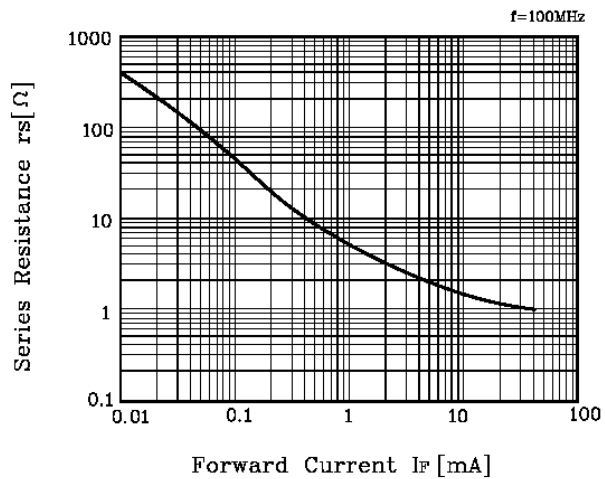


Fig. 4 r_s - I_F

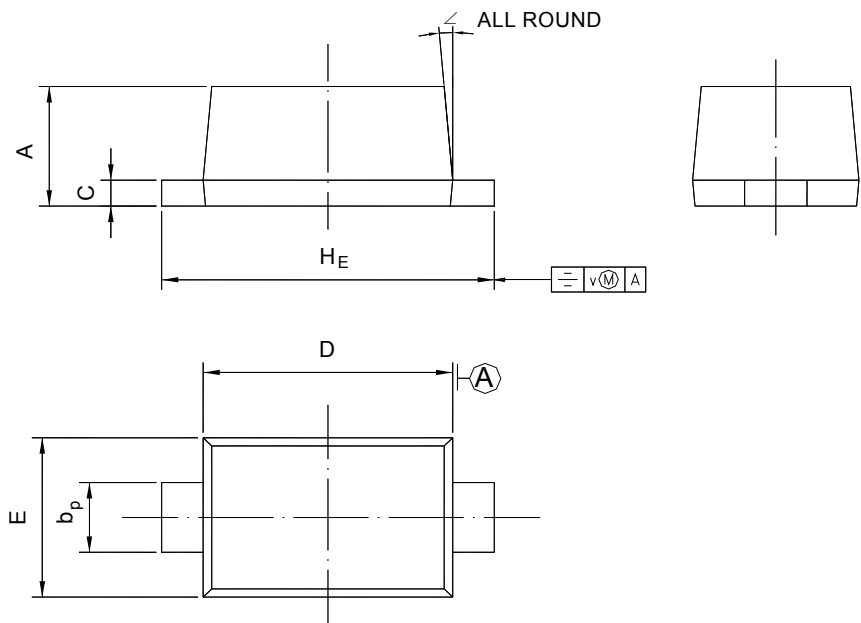


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

